



Pulse Power Thyristor Switch

Preliminary Information

 V_{DRM}

I_{T(AV)}

I_{TSM}

DS5267-1.4 April 2000

KEY PARAMETERS

4500V

13000A

5000A/μs

760A

Replaces November 1999 version, DS5267-1.1

APPLICATIONS

- Pulse Power
- Crowbars
- Ignitron Replacement

FEATURES

- Double Side Cooling
- Fast Turn-on
- Low Turn-on Losses

VOLTAGE RATINGS

Type Number	Repetitive Peak Voltages V _{DRM} /V _{RRM} V	Conditions
PT40QPx45	4500/16	$\begin{split} T_{vj} &= 0^{\circ} \text{ to } 125^{\circ}\text{C}, \\ I_{DRM} &= I_{RRM} = 50\text{mA}, \\ V_{DRM}, V_{RRM} t_{p} &= 10\text{ms} \end{split}$

Lower voltage grades available.

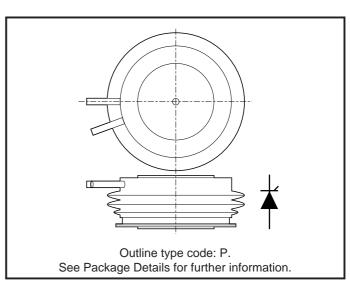


Fig.1 Package outline

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units	
Double Sid	Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load, T _{case} = 80°C	760	А	
I _{T(RMS)}	RMS value	$T_{case} = 80$ °C	1190	А	

PT40QPx45

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	10.4	kA
l ² t	I ² t for fusing	$V_{R} = 50\% V_{RRM} - 1/4 \text{ sine}$	541 x 10 ³	A²s
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine; T _{case} = 125°C	13.0	kA
l ² t	I ² t for fusing	V _R = 0	845 x 10 ³	A²s

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance - junction to case	Double side cooled	dc	-	0.033	°C/W
R _{th(c-h)}	Thermal resistance - case to heatsink	Clamping force 12.0kN with mounting compound	Double side	-	0.008	°C/W
_	Vintual impation to one out the	On-state (conducting)		-	135	°C
$T_{v_{j}}$	Virtual junction temperature	Reverse (blocking)		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
-	Clamping force			11.0	15.0	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Conditions	i	Тур.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	50	mA
dV/dt	Maximum linear rate of rise of off-state voltage	To 67% V_{DRM} T_j = 125°C. $R_{gk} \le 1.5Ω$		-	200	V/µs
dI/dt	Rate of rise of on-state current	From 67% V_{DRM} to 20kA Gate source 30A $t_r = 1.5 \mu s$, $T_j = 25 ^{\circ} C$	Non-repetitive	-	5000	A/μs
V _{T(TO)}	Threshold voltage	At T _{vj} = 125°C		-	1.4	V
r _T	On-state slope resistance	At T _{vj} = 125°C		-	0.152	mΩ

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Conditions	Тур.	Max.	Units
V _{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.0	4.0	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	-	1.5	Α

ORDERING INFORMATION

PT Pulse Power Thyristor

40Q Device type

P Package outline type code x lead length (see table, right)

45 Voltage x100

Lead length (x)				
0	No lead			
С	8"	200mm		
D	10"	250mm		
E	12"	300mm		
F	16"	400mm		
G	18"	450mm		
Н	20"	500mm		
J	24"	600mm		
K	30"	750mm		
L	40"	1000mm		

CURVES

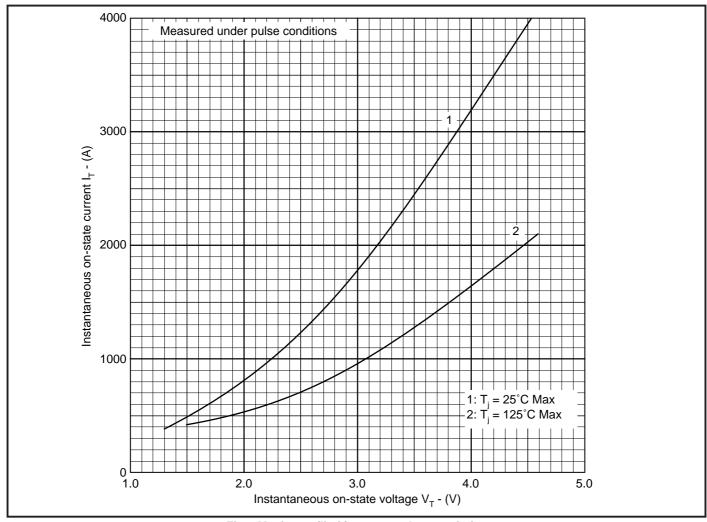


Fig.2 Maximum (limit) on-state characteristics

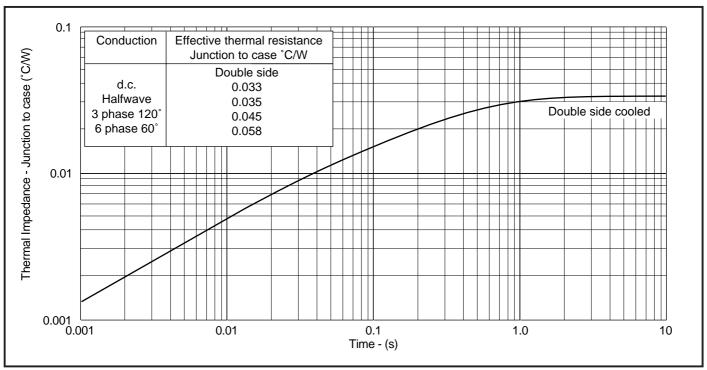
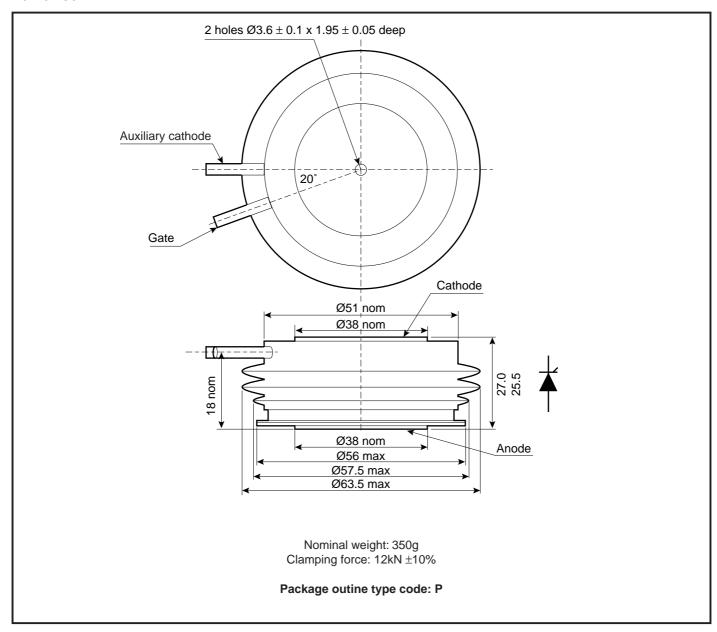


Fig.3 Maximum (limit) transient thermal impedance - junction to case

PACKAGE DETAILS

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

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For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



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